



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(ON) Max	I _D T _A = +25°C
-30V	$70m\Omega @V_{GS} = -10V$	-3.4A
-30 V	130mΩ @V _{GS} = -4.5V	-2.5A

Description

This MOSFET is designed to minimize on-state resistance (Rds(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Load switches
- Power management functions

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

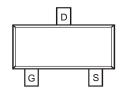
Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

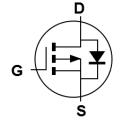
SOT23







Pin Configuration



Equivalent Circuit

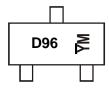
Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Number	Fackage	Qty.	Carrier	
DMP3096L-7	SOT23	3,000	Tape & Reel	
DMP3096L-13	SOT23	10.000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at https://www.diodes.com/design/support/packaging/.

Marking Information



 $\underline{\underline{D96}} = \text{Product Type Marking Code}$ $\underline{\underline{YM}} = \text{Date Code Marking}$ $\underline{\underline{Y}} = \text{Year (ex: } J = 2022)$ $\underline{M} = \text{Month (ex: } N = \text{November)}$

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	N	0	Р	R	S	T	U	V
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		VDSS	-30	V
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	-3.4 -2.7	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle =	I _{DM}	-22	А	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	8.0	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	Reja	158	°C/W
Power Dissipation (Note 6)	PD	1.2	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{θJA}	100	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

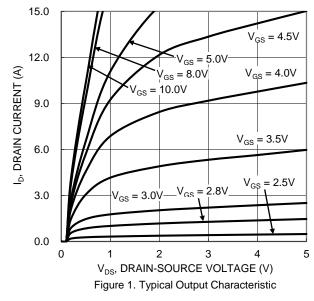
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			- 76			Tota of indicate
Drain-Source Breakdown Voltage	BVDSS	-30	_	_	V	V _G S = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-800	nA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0		-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance	Pro/own		48	70	mΩ	$V_{GS} = -10V, I_D = -3.8A$
Static Drain-Source On-Resistance	RDS(ON)		83	130	11122	$V_{GS} = -4.5V$, $I_D = -3.0A$
Diode Forward Voltage	VsD		-0.8	-1.26	V	Vgs = 0V, Is = -2.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		366	_	pF	
Output Capacitance	Coss		51	_	pF	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1.0MHz$
Reverse Transfer Capacitance	Crss		39	_	pF	
Gate Resistance	Rg		9.2	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg		3.8	_		
Total Gate Charge (V _{GS} = -10V)	Qg	_	7.5	_	nC	V _{DS} = -15V, I _D = -3.8A
Gate-Source Charge	Qgs	_	1.0	_	IIC	
Gate-Drain Charge	Q_{gd}		1.1	_		
Turn-On Delay Time	t _{d(on)}	_	3.2	_		
Rise Time	t _r	_	8.2			V _{DS} = -15V, V _{GS} = -10V,
Turn-Off Delay Time	t _{d(off)}		21.7		ns	$I_D = -1A$, $R_G = 6.0\Omega$
Fall Time	tf	_	13.1			

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.





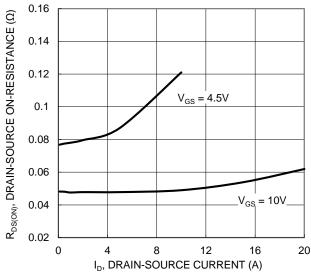


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

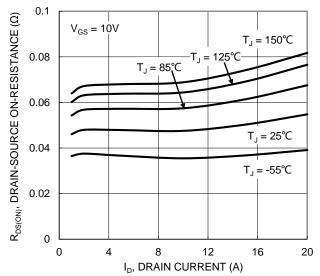
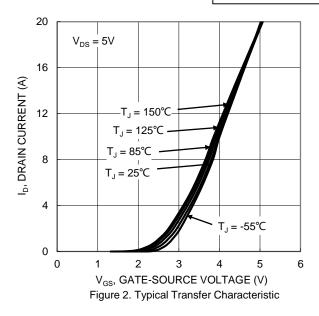
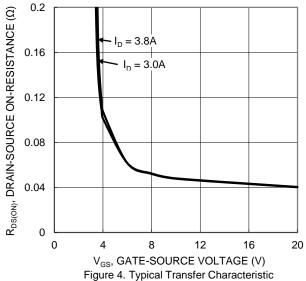


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





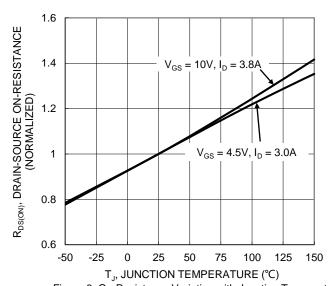


Figure 6. On-Resistance Variation with Junction Temperature



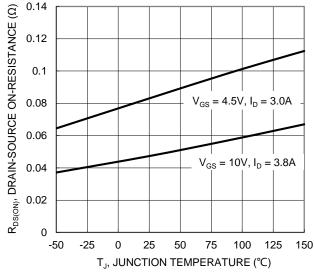
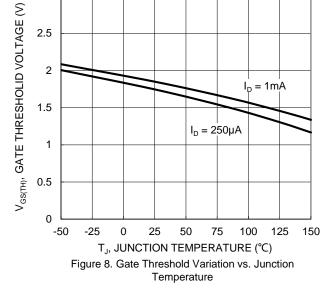
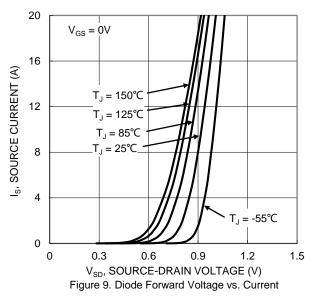


Figure 7. On-Resistance Variation with Junction Temperature



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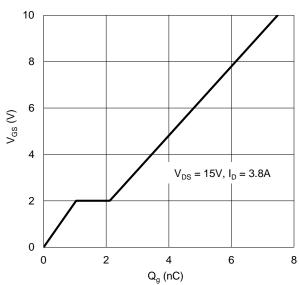
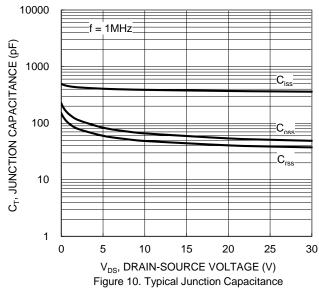
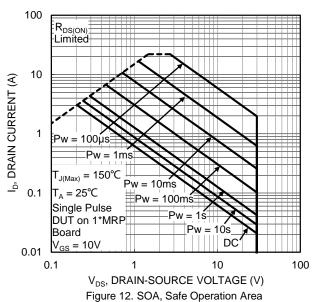
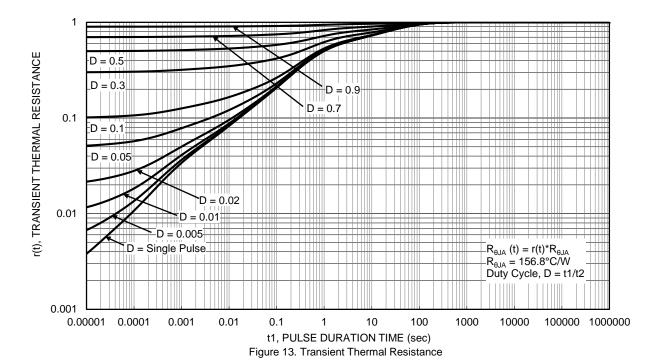


Figure 11. Gate Charge







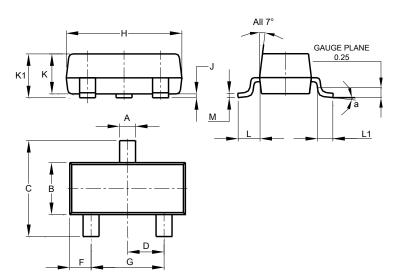




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

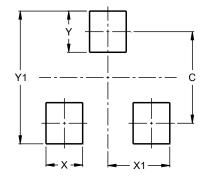


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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